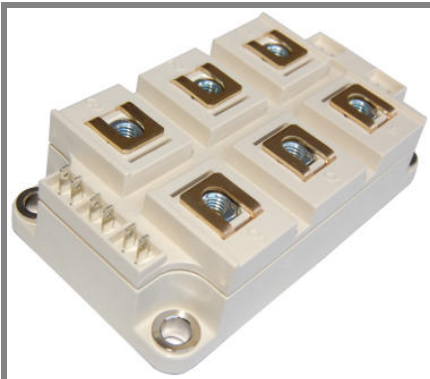


SKM 150 MLI 066 T



SEMITRANS® 5

Trench IGBT Modules

SKM 150 MLI 066 T

Target Data

Features

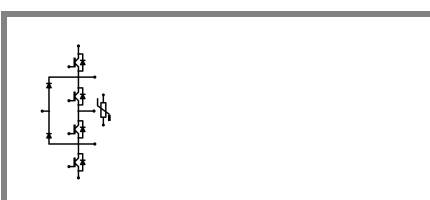
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- Integrated NTC temperature sensor

Typical Applications*

- UPS
- 3 Level Inverter

Remarks

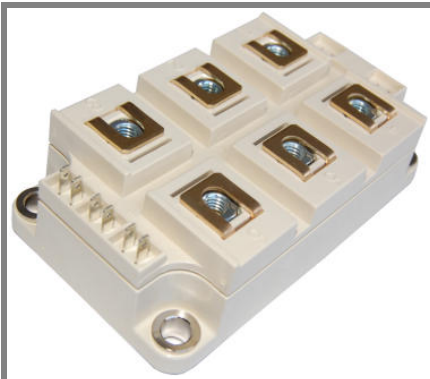
- Case temperature limited to $T_c = 125^\circ\text{C}$ max, recommended $T_{op} = -40..+150^\circ\text{C}$



MLI-T

Absolute Maximum Ratings		$T_{case} = 25^\circ\text{C}$, unless otherwise specified		
Symbol	Conditions	Values		Units
IGBT				
V_{CES}	$T_j = 25^\circ\text{C}$	600		V
I_C	$T_j = 175^\circ\text{C}$	$T_c = 25^\circ\text{C}$	200	A
		$T_c = 80^\circ\text{C}$	150	A
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	300		A
V_{GES}		± 20		V
t_{psc}	$V_{CC} = 360\text{ V}; V_{GE} \leq 15\text{ V}; T_j = 150^\circ\text{C}$ $V_{CES} < 600\text{ V}$	6		μs
Inverse Diode				
I_F	$T_j = 150^\circ\text{C}$	$T_c = 25^\circ\text{C}$	200	A
		$T_c = 80^\circ\text{C}$	145	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	300		A
I_{FSM}	$t_p = 10\text{ ms};$ half sine wave $T_j = 150^\circ\text{C}$	1080		A
Freewheeling Diode				
I_F	$T_j = 150^\circ\text{C}$	$T_c = 25^\circ\text{C}$	200	A
		$T_c = 80^\circ\text{C}$	145	A
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	300		A
I_{FSM}	$t_p = 10\text{ ms};$ half sine wave $T_j = 150^\circ\text{C}$	1080		A
Module				
$I_{t(RMS)}$		500		A
T_{vj}		- 40 ... + 175		$^\circ\text{C}$
T_{stg}		- 40 ... + 125		$^\circ\text{C}$
V_{isol}	AC, 1 min.	2500		V

Characteristics		$T_{case} = 25^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 2,4\text{ mA}$	5	5,8	6,5	V
I_{CES}	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$ $T_j = 25^\circ\text{C}$			0,0076	mA
I_{GES}	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$ $T_j = 25^\circ\text{C}$			600	nA
V_{CE0}		$T_j = 25^\circ\text{C}$	0,9	1	V
		$T_j = 150^\circ\text{C}$	0,85	0,9	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	3,6	6	$\text{m}\Omega$
		$T_j = 150^\circ\text{C}$	5,4	7,6	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 150\text{ A}, V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}_{chiplev.}$	1,45	1,9	V
		$T_j = 150^\circ\text{C}_{chiplev.}$	1,7	2,1	V
C_{ies}	$V_{CE} = 25, V_{GE} = 0\text{ V}$ $f = 1\text{ MHz}$		9,2		nF
C_{oes}			0,57		nF
C_{res}			0,27		nF
R_{Gint}	$T_j = ^\circ\text{C}$		2		Ω
$t_{d(on)}$	$R_{Gon} = 2\ \Omega$	$V_{CC} = 300\text{ V}$ $I_C = 150\text{ A}$	0,7		ns
t_r					ns
E_{on}	$R_{Goff} = 4\ \Omega$	$T_j = 150^\circ\text{C}$ $V_{GE} = -8\text{ V}/+15\text{ V}$	4,7		mJ
$t_{d(off)}$					ns
t_f					ns
E_{off}					mJ
$R_{th(j-c)}$	per IGBT		0,29		K/W



SEMITRANS[®] 5

Trench IGBT Modules

SKM 150 MLI 066 T

Target Data

Features

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- Integrated NTC temperature sensor

Typical Applications*

- UPS
- 3 Level Inverter

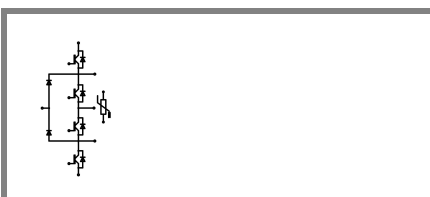
Remarks

- Case temperature limited to $T_C = 125^\circ\text{C}$ max, recommended $T_{op} = -40..+150^\circ\text{C}$

Characteristics							
Symbol	Conditions			min.	typ.	max.	Units
Inverse Diode							
$V_F = V_{EC}$	$I_{Fnom} = 150\text{ A}; V_{GE} = 0\text{ V}$	$T_j = 25^\circ\text{C}_{chiplev.}$			1,35	1,6	V
		$T_j = 150^\circ\text{C}_{chiplev.}$			1,35	1,6	V
V_{F0}		$T_j = 25^\circ\text{C}$			1	1,1	V
		$T_j = 150^\circ\text{C}$			0,9	1	V
r_F		$T_j = 25^\circ\text{C}$			2,3	3,3	mΩ
		$T_j = 150^\circ\text{C}$			3	4	mΩ
I_{RRM}	$I_F = 150\text{ A}$	$T_j = 150^\circ\text{C}$					A
Q_{rr}							μC
E_{rr}	$V_{GE} = -8\text{ V}; V_{CC} = 300\text{ V}$						mJ
$R_{th(j-c)D}$	per diode				0,52		K/W
Free-wheeling diode (Neutral Clamp Diode)							
$V_F = V_{EC}$	$I_{Fnom} = 150\text{ A}; V_{GE} = 0\text{ V}$	$T_j = 25^\circ\text{C}_{chiplev.}$			1,35	1,6	V
		$T_j = 150^\circ\text{C}_{chiplev.}$			1,35	1,6	V
V_{F0}		$T_j = 25^\circ\text{C}$			1	1,1	V
		$T_j = 150^\circ\text{C}$			0,9	1	V
r_F		$T_j = 25^\circ\text{C}$			2,3	3,3	V
		$T_j = 150^\circ\text{C}$			3	4	V
I_{RRM}	$I_F = 150\text{ A}$	$T_j = 150^\circ\text{C}$					A
Q_{rr}							μC
E_{rr}	$V_{GE} = 0\text{ V}; V_{CC} = 600\text{ V}$						mJ
$R_{th(j-c)FD}$	per diode				0,52		K/W
$R_{th(c-s)}$	per module					0,038	K/W
M_s	to heat sink M6			3		5	Nm
M_t	to terminals M6			2,5		5	Nm
w						310	g
Temperature sensor							
R_{100}	$T_s = 100^\circ\text{C}$ ($R_{25} = 5\text{k}\Omega$)				493±5%		Ω K

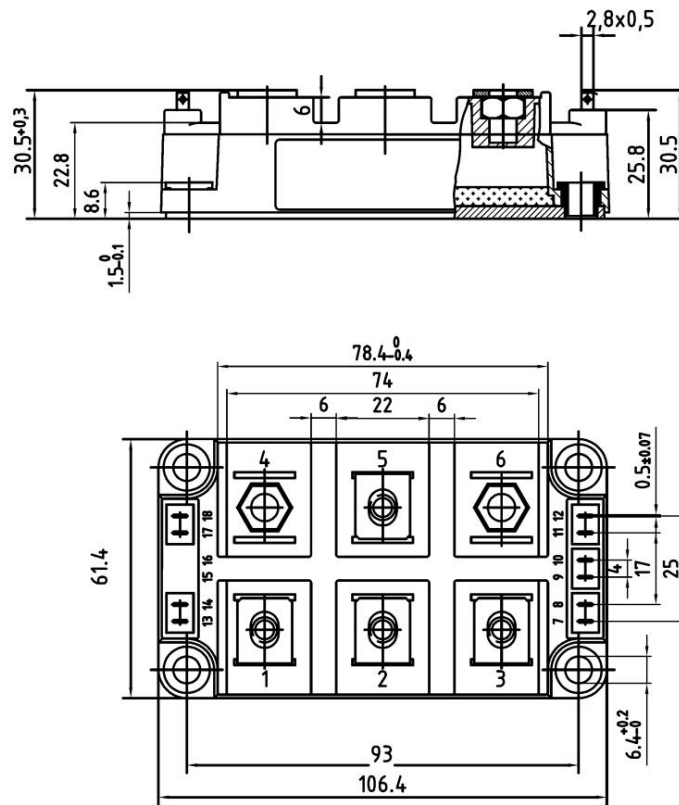
This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

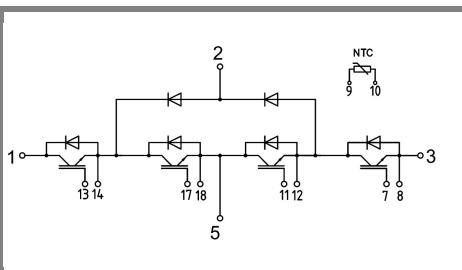


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SKM 150 MLI 066 T



Case D60



MLI-T

Case D60